SGN2731-500L-R S-band Internally Matched GaN-HEMT

Features

High Power: 550W(Typ.) @ Pin=28.2W(44.5dBm)
High Efficiency: 57%(Typ.) @ Pin=28.2W(44.5dBm)

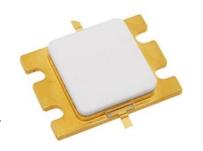
· Broad Band: 2.7 to 3.1GHz

• Impedance Matched Zin/Zout = 50 ohm

· Hermetically Sealed Package



Sumitomo Electric's GaN-HEMT SGN2731-500L-R offers high power, high efficiency and greater consistency covering 2.7 to 3.1 GHz for S-band radar applications with 50V operation.



ABSOLUTE MAXIMUM RATING (Case Temperature Tc=25 deg.C)

<u> </u>			
Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	55	V
Gate-Source Voltage	V _{GS}	-15	V
Storage Temperature	T _{stg}	-55 to +125	deg.C
Channel Temperature	Tch	+250	deg.C

RECOMMENDED OPERATING CONDITION

RECOMMENDED OF ERATING CONDITION						
Item	Symbol	Condition	Limit	Unit		
Drain-Source Voltage	V _{DS}		<=50	V		
Forward Gate Current	Igf	Rg=5.1ohm	<=304	mA		
Reverse Gate Current	Igr	Rg=5.1ohm	>=-18	mA		
Channel Temperature	Tch		<+200	deg.C		
Output Power	Pout	_	<=P5dB	dBm		

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25 deg.C)

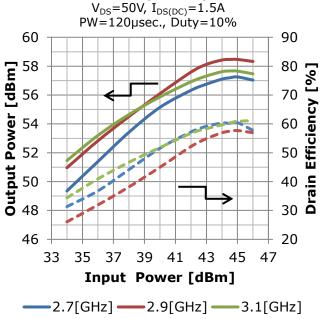
Item	Symbol	Condition	Limit			Unit
			Min.	Тур.	Max.	Unit
Pinch-off Voltage	Vp	V _{DS} =50V, I _{DS} =115mA	-3.45	-3.00	-2.45	V
Frequency Range	Freq.	V _{DS} =50V-typ. I _{DS(DC)} =1.5A-typ. Pulse Width=120µsec. Duty=10% Pin=44.5dBm	2.7	1	3.1	GHz
Output Power	P _{sat}		56.8	57.4	-	dBm
Power Gain	Gp		12.3	12.9	-	dB
Gain Flatness	GF		ı	1.3	-	dB
Drain Efficiency	DE		ı	57	-	%
Load Mismatch Ruggedness	VSWR		ı	10:1	-	-
Thermal Resistance	R _{th}	Channel to Case at 105W PDC	-	0.55	0.7	deg.C/W

CASE STYLE	IV
RoHS Compliance	YES



■ RF Characteristics

Output Power & Drain Efficiency vs. Input Power



Output Power vs. Input Power by Drain Voltage f=2.9GHz, I_{DS(DC)}=1.5A

PW=120µsec., Duty=10% 60 58 Output Power [dBm] 56 54 52 50 48 46 32 34 36 38 40 42 44 46 Input Power [dBm]

-35V

-50V

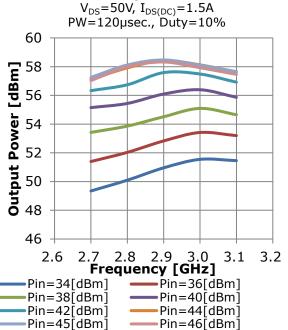
-40V

---55V

30V

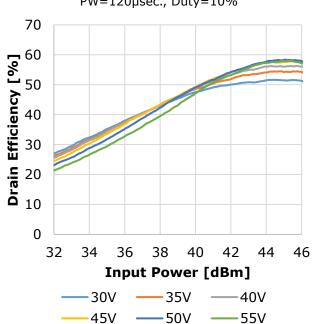
45V

Output Power vs. Frequency by Pin



Drain Efficiency vs. Input Power by Drain Voltage

f=2.9GHz, I_{DS(DC)}=1.5A PW=120µsec., Duty=10%





60

58

56

54

52 50

48

46 44

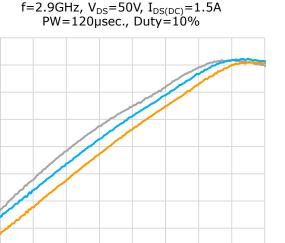
30

32

Output Power [dBm]

■ RF Characteristics

Output Power vs. Input Power by case temperature



—-40 deg.C —-25 deg.C —-85 deg.C

38

Input Power [dBm]

40

42

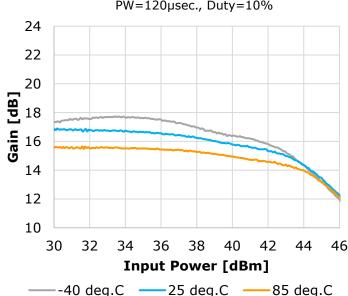
44

46

36

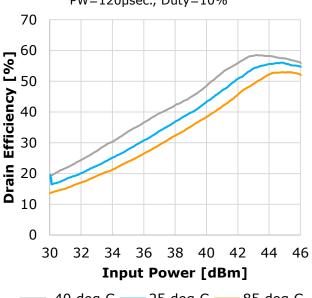
Gain vs. Input Power by case temperature

f=2.9GHz, V_{DS}=50V, I_{DS(DC)}=1.5A PW=120µsec., Duty=10%



Drain Efficiency vs. Input Power by case temperature

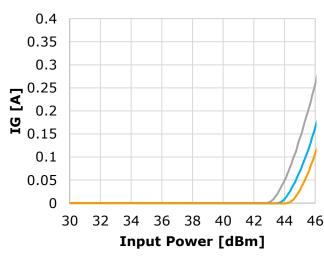
f=2.9GHz, V_{DS} =50V, $I_{DS(DC)}$ =1.5A PW=120 μ sec., Duty=10%



-40 deg.C — 25 deg.C — 85 deg.C

IG vs. Input Power by case temperature

f=2.9GHz, V_{DS} =50V, $I_{DS(DC)}$ =1.5A PW=120 μ sec., Duty=10%

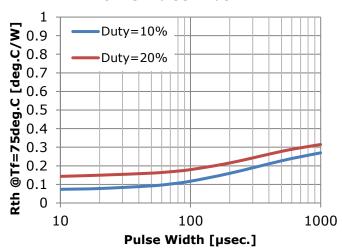


—-40 deg.C ——25 deg.C ——85 deg.C



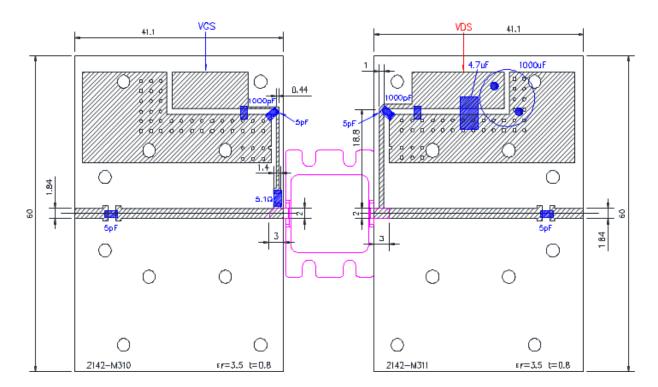
■ Thermal Characteristics In Pulsed Operation

Rth vs. Pulse Width





■ Test Fixture



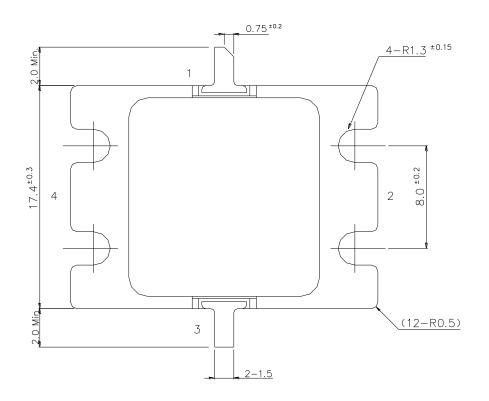
PCB: h=0.8mm, er=3.5, Cu=18um

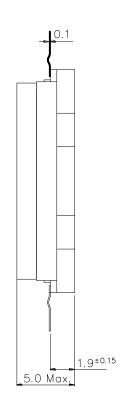
Unit: mm

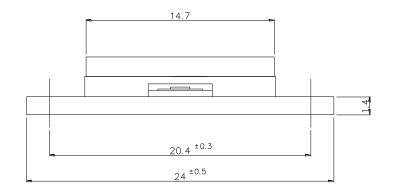


■ Package Outline

Case Style: IV







1:Gate

2:Source(Flange)

3:Drain

4:Source(Flange)

Unit : mm



For Safety, Observe the Following Procedures Environmental Management

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.
 This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

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